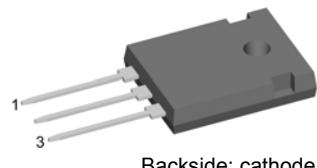
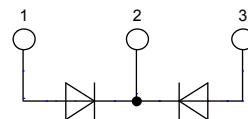


Sonic Fast Recovery Diode

High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Common Cathode

Part number

DHG 60 C 600 HB



Backside: cathode

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package:

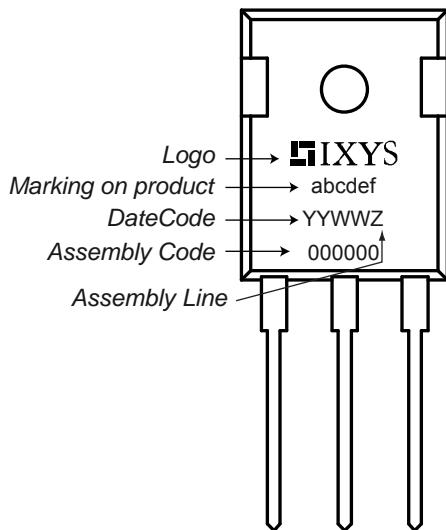
- Housing: TO-247
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RRM}	max. repetitive reverse voltage					600	V
I_R	reverse current	$V_R = 600\text{ V}$	$T_{VJ} = 25^\circ\text{C}$			30	μA
		$V_R = 600\text{ V}$	$T_{VJ} = 125^\circ\text{C}$			2	mA
V_F	forward voltage	$I_F = 30\text{ A}$	$T_{VJ} = 25^\circ\text{C}$			2.26	V
		$I_F = 60\text{ A}$				3.11	V
		$I_F = 30\text{ A}$	$T_{VJ} = 125^\circ\text{C}$			2.21	V
		$I_F = 60\text{ A}$				3.17	V
I_{FAV}	average forward current	rectangular	$d = 0.5$	$T_c = 85^\circ\text{C}$		30	A
V_{FO}	threshold voltage	$\left. \begin{array}{l} V_F \\ r_F \end{array} \right\}$ slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ\text{C}$		1.17	V
r_F	slope resistance					31	$\text{m}\Omega$
R_{thJC}	thermal resistance junction to case					0.70	K/W
T_{VJ}	virtual junction temperature			-55		150	$^\circ\text{C}$
P_{tot}	total power dissipation					180	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}$ (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		200	A
I_{RM}	max. reverse recovery current			$T_{VJ} = 25^\circ\text{C}$		13	A
		$I_F = 30\text{ A}; V_R = 300\text{ V}$		$T_{VJ} = 125^\circ\text{C}$		17	A
t_{rr}	reverse recovery time	$-di_F/dt = 600\text{ A}/\mu\text{s}$		$T_{VJ} = 25^\circ\text{C}$		40	ns
				$T_{VJ} = 125^\circ\text{C}$		60	ns
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$		$T_{VJ} = 25^\circ\text{C}$		16	pF

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	RMS current	per terminal ¹⁾			70	A
R_{thCH}	thermal resistance case to heatsink			0.25		K/W
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_c	mounting force with clip		20		120	N

¹⁾ I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2).
In case of (1) and a common cathode/anode configuration with a non-isolated backside,
the current capability can be increased by connecting the backside.

Product Marking



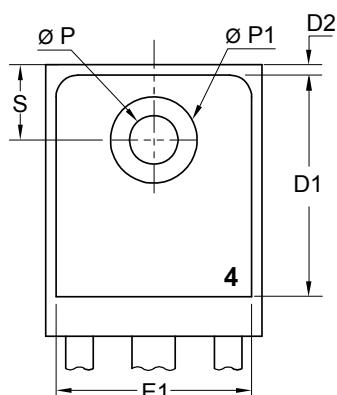
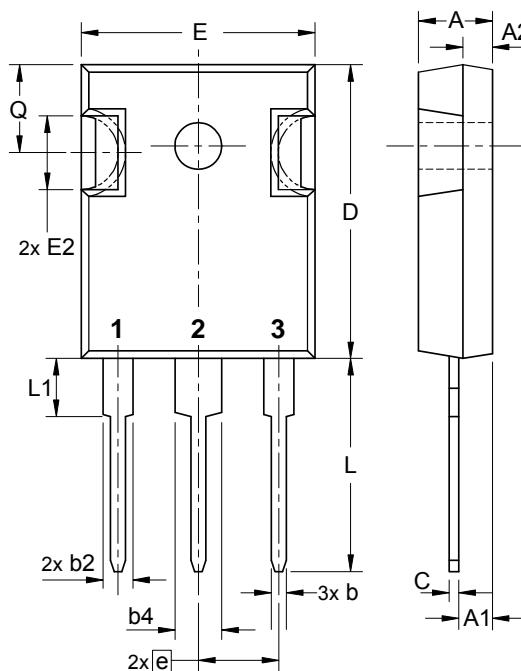
Part number

D = Diode
 H = Sonic Fast Recovery Diode
 G = extreme fast
 60 = Current Rating [A]
 C = Common Cathode
 600 = Reverse Voltage [V]
 HB = TO-247AD (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG 60 C 600 HB	DHG60C600HB	Tube	30	503108

Similar Part	Package	Voltage Class
DSEC60-06A	TO-247AD (3)	600
DSEC60-06B	TO-247AD (3)	600
DSEC59-06BC	ISOPPLUS220AB (3)	600

Outlines TO-247



Sym.	Inches min. max.	Millimeter min. max.
A	0.185 0.209	4.70 5.30
A1	0.087 0.102	2.21 2.59
A2	0.059 0.098	1.50 2.49
D	0.819 0.845	20.79 21.45
E	0.610 0.640	15.48 16.24
E2	0.170 0.216	4.31 5.48
e	0.215 BSC	5.46 BSC
L	0.780 0.800	19.80 20.30
L1	- 0.177	- 4.49
Ø P	0.140 0.144	3.55 3.65
Q	0.212 0.244	5.38 6.19
S	0.242 BSC	6.14 BSC
b	0.039 0.055	0.99 1.40
b2	0.065 0.094	1.65 2.39
b4	0.102 0.135	2.59 3.43
c	0.015 0.035	0.38 0.89
D1	0.515 -	13.07 -
D2	0.020 0.053	0.51 1.35
E1	0.530 -	13.45 -
Ø P1	- 0.29	- 7.39

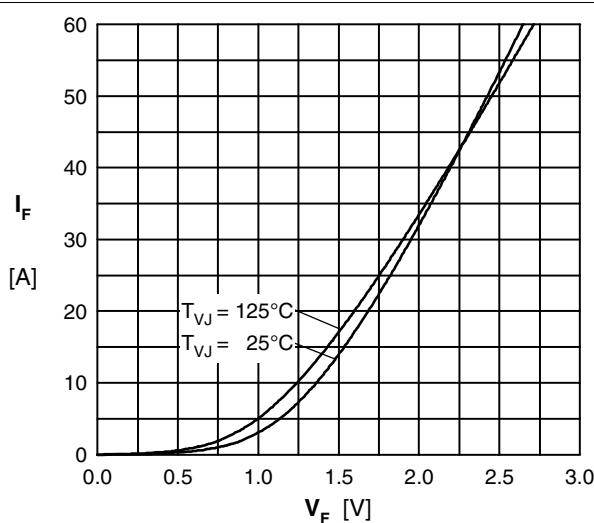
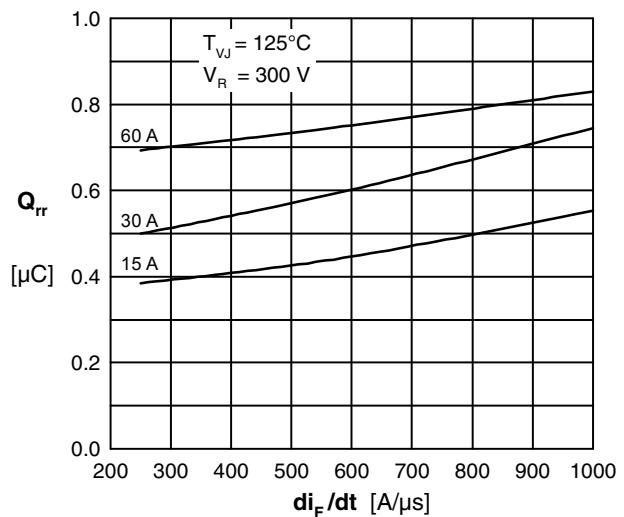
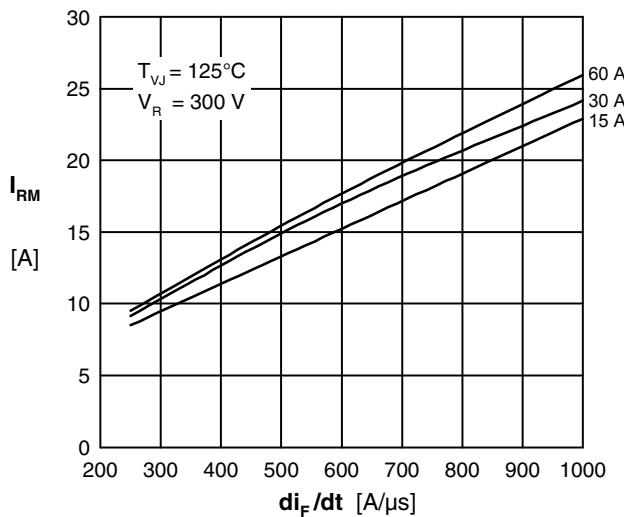
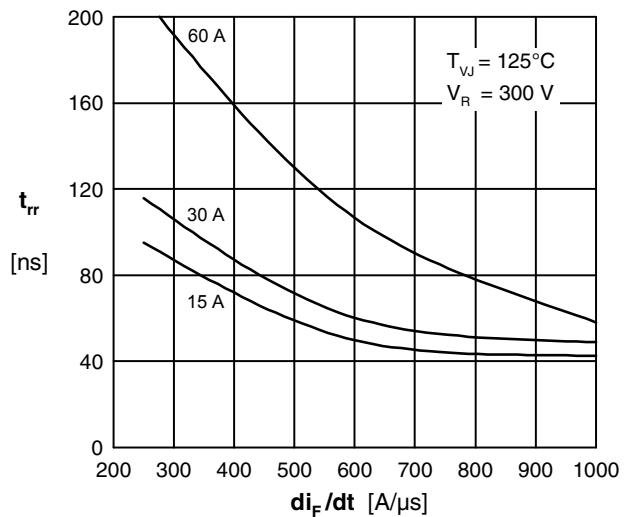
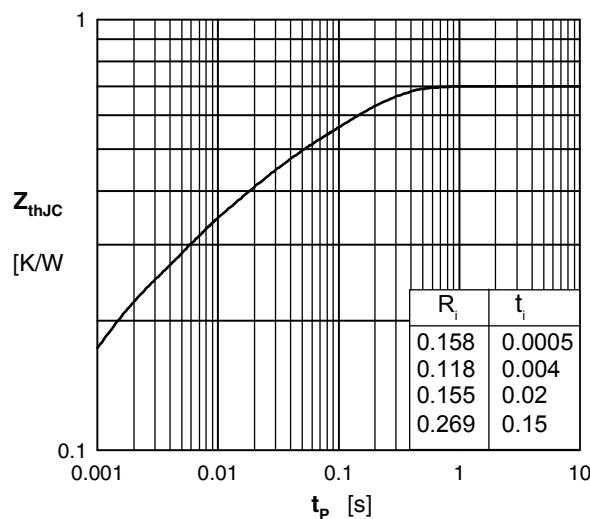
Fig. 1 Typ. Forward current versus V_F Fig. 2 Typ. reverse recov.charge Q_{rr} vs. di/dt Fig. 3 Typ. peak reverse current I_{RM} vs. di/dt Fig. 4 Typ. recovery time t_{rr} versus di/dt 

Fig. 5 Transient thermal impedance